DATA SHEET

# NEC

# MOS FIELD EFFECT TRANSISTOR **QN7002**

2.9±0.2

2

0 95

0.4<sup>+0.1</sup>

ρ. 05

3

0.95

# **N-CHANNEL MOSFET** FOR SWITCHING

22

o c + 1

65 -

ö

 $0.4^{+0.1}_{-0.05}$ 

N 8±0. s

N

#### DESCRIPTION

The QN7002, N-channel vertical type MOSFET designed for general-purpose switch, is a device which can be driven directly by a 4.5 V power source.

#### **FEATURES**

- Directly driven by a 4.5 V power source.
- Low on-state resistance

 $R_{DS(on)1} = 2.7 \Omega MAX. (V_{GS} = 10 V, I_D = 100 mA)$  $R_{DS(on)2}$  = 3.2  $\Omega$  MAX. (V<sub>GS</sub> = 4.5 V, I<sub>D</sub> = 50 mA)

#### **ORDERING INFORMATION**

PART NUMBER	PACKAGE		
QN7002-T1B-AT	SC-59 (Mini Mold)		
QN7002-T2B-AT			

Remark "-AT" indicates Pb-free.

This product dose not contain Pb external electrode and other parts. 8 mm embossed carrier tape, 3,000 pcs/reel.





1 to 1.4

0.3

0 to 0.1

1. Source

2. Gate 3. Drain

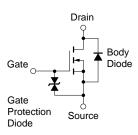
Remark for Agent ORDER NUMBER "2SK4079A(1)" must be used to order, instead of "QN7002". For instance, "2SK4079A(1)-T1B-AT".

#### Marking: G28

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ )

Drain to Source Voltage (Vgs = 0 V)	VDSS	60	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±20	V
Drain Current (DC)	D(DC)	200	mA
Drain Current (pulse) <sup>Note</sup>	D(pulse)	±800	mA
Total Power Dissipation	Ρτ	200	mW
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C





**Note** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

Caution This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge.

VESD ±400 V (MIL STD; C = 100 pF, R = 1.5 k $\Omega$ , 5 times), as reference value.

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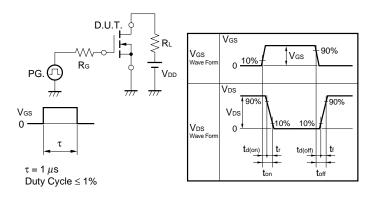
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CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	Ibss	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	μA
Gate Leakage Current	Igss	$V_{GS} = \pm 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			±10	μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μ/Α	1.0		2.5	V
Forward Transfer Admittance Note	yfs	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 100 mA	150			mS
Drain to Source On-state Resistance <sup>Note</sup>	RDS(on)1	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 100 mA		2.1	2.7	Ω
	RDS(on)2	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 50 mA		2.4	3.2	Ω
Input Capacitance	Ciss	V <sub>DS</sub> = 10 V,		20		pF
Output Capacitance	Coss	V <sub>GS</sub> = 0 V,		9		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		2		pF
Turn-on Delay Time	td(on)	V <sub>DD</sub> = 10 V,		16		ns
Rise Time	tr	I⊳ = 200 mA,		6.5		ns
Turn-off Delay Time	td(off)	V <sub>GS</sub> = 10 V,		82		ns
Fall Time	tr	R <sub>G</sub> = 10 Ω		32		ns
Total Gate Charge	QG	$I_D$ = 200 mA, $V_{DD}$ = 25 V, $V_{GS}$ = 10 V		2		nC
Body Diode Forward Voltage <sup>Note</sup>	VF(S-D)	IF = 200 mA, V <sub>GS</sub> = 0 V		0.86		V

## ELECTRICAL CHARACTERISTICS (TA = 25°C)

Note Pulsed

# **TEST CIRCUIT SWITCHING TIME**



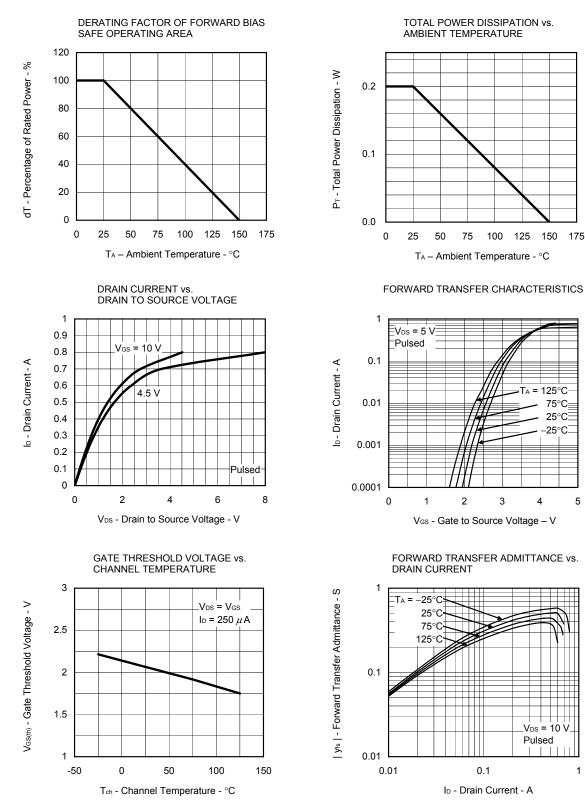
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75°C₌ 25°C

25°C

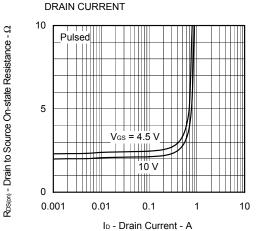
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### TYPICAL CHARACTERISTICS (TA = 25°C)



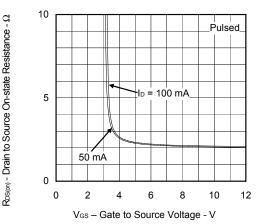
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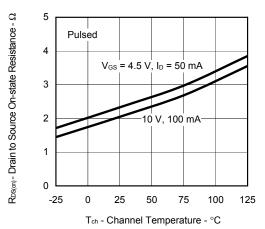


DRAIN TO SOURCE ON-STATE RESISTANCE vs.

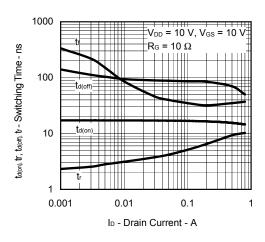
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

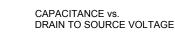


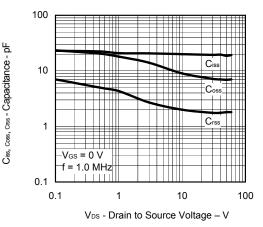
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

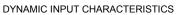


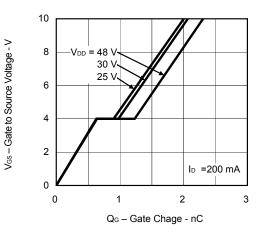








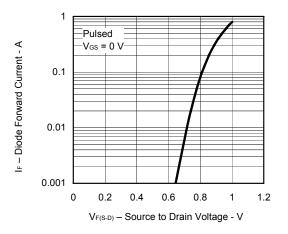




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#### SOURCE TO DRAIN DIODE FORWARD VOLTAGE

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